

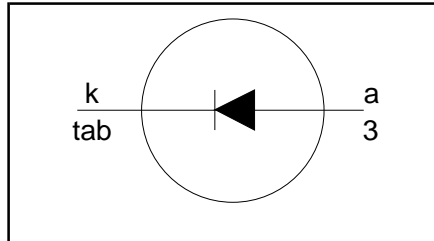
**Rectifier diodes  
Schottky barrier**

**PBYR1025D series**

**FEATURES**

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

**SYMBOL**



**QUICK REFERENCE DATA**

$V_R = 20\text{ V} / 25\text{ V}$
$I_{F(AV)} = 10\text{ A}$
$V_F \leq 0.41\text{ V}$

**GENERAL DESCRIPTION**

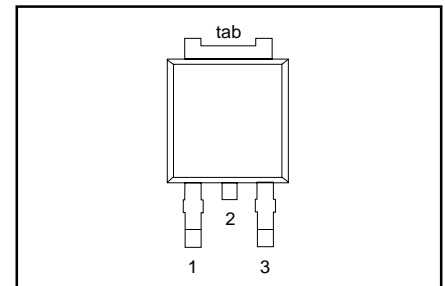
Schottky rectifier diodes in a surface mounting plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR1025D series is supplied in the SOT428 surface mounting package.

**PINNING**

PIN	DESCRIPTION
1	no connection
2	cathode <sup>1</sup>
3	anode
tab	cathode

**SOT428**



**LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
				PBYR10		
$V_{RRM}$	Peak repetitive reverse voltage		-	<b>20D</b> 20	<b>25D</b> 25	V
$V_{RWM}$	Working peak reverse voltage		-	20	25	V
$V_R$	Continuous reverse voltage	$T_{mb} \leq 120\text{ °C}$	-	20	25	V
$I_{F(AV)}$	Average rectified forward current	square wave; $\delta = 0.5$ ; $T_{mb} \leq 140\text{ °C}$	-	10		A
$I_{FRM}$	Repetitive peak forward current	square wave; $\delta = 0.5$ ; $T_{mb} \leq 140\text{ °C}$	-	20		A
$I_{FSM}$	Non-repetitive peak forward current	$t = 10\text{ ms}$	-	100		A
		$t = 8.3\text{ ms}$	-	110		A
$I_{RRM}$	Peak repetitive reverse surge current	sinusoidal; $T_j = 125\text{ °C}$ prior to surge; with reapplied $V_{RRM(max)}$ pulse width and repetition rate limited by $T_{jmax}$	-	1		A
$T_j$	Operating junction temperature		-	150		°C
$T_{stg}$	Storage temperature		- 65	175		°C

<sup>1</sup> It is not possible to make connection to pin 2 of the SOT428 package.

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	pcb mounted, minimum footprint, FR4 board	-	-	2	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient		-	50	-	K/W

### ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_F$	Forward voltage	$I_F = 10\text{ A}; T_j = 125\text{ }^\circ\text{C}$	-	0.33	0.41	V
		$I_F = 20\text{ A}; T_j = 125\text{ }^\circ\text{C}$	-	0.43	0.55	V
		$I_F = 20\text{ A}$	-	0.51	0.6	V
$I_R$	Reverse current	$V_R = V_{RWM}$	-	1	5	mA
		$V_R = V_{RWM}; T_j = 100\text{ }^\circ\text{C}$	-	22	40	mA
$C_d$	Junction capacitance	$V_R = 5\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C to } 125\text{ }^\circ\text{C}$	-	700	-	pF

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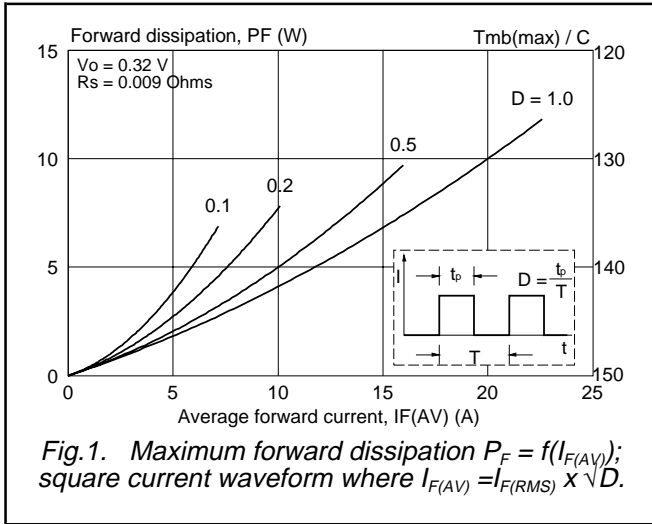


Fig.1. Maximum forward dissipation  $P_F = f(I_{F(AV)})$ ; square current waveform where  $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$ .

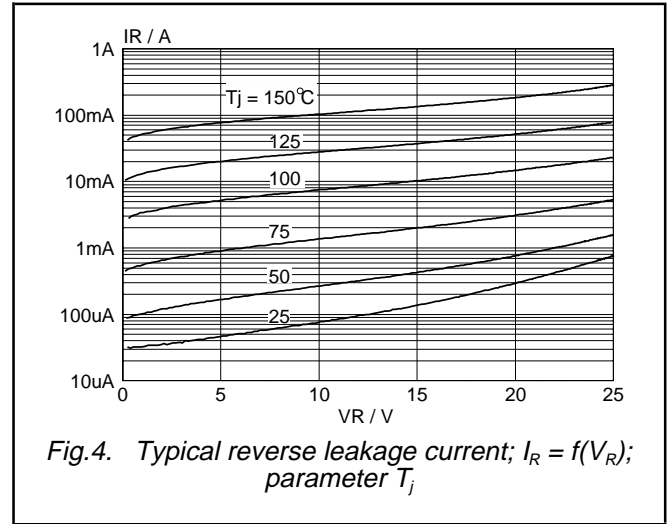


Fig.4. Typical reverse leakage current;  $I_R = f(V_R)$ ; parameter  $T_j$

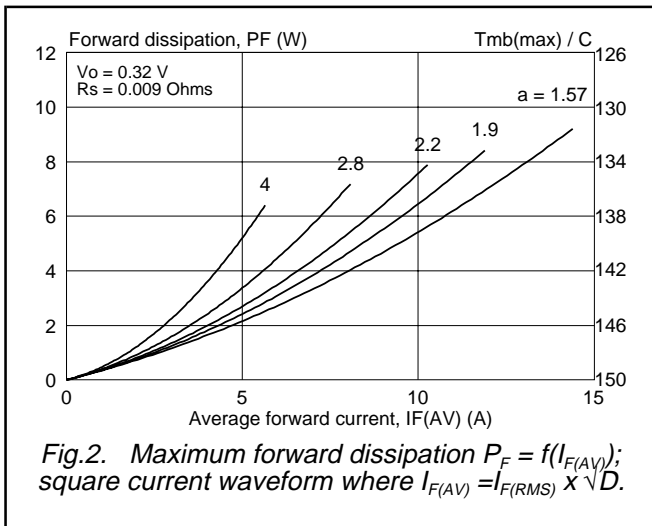


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$ ; square current waveform where  $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$ .

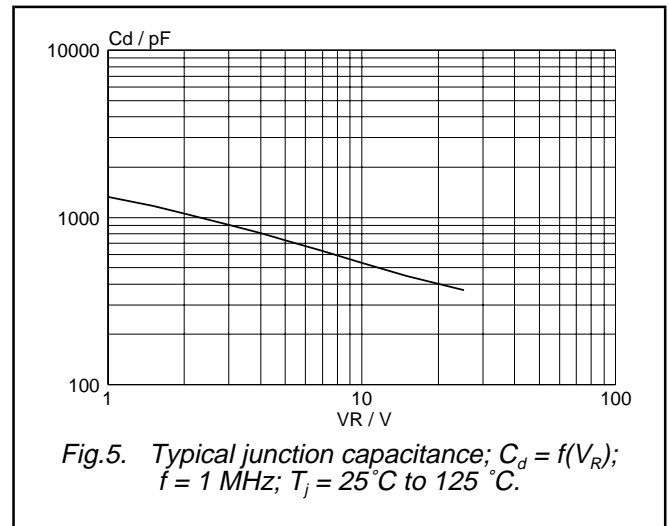


Fig.5. Typical junction capacitance;  $C_d = f(V_R)$ ;  $f = 1 \text{ MHz}$ ;  $T_j = 25^\circ\text{C}$  to  $125^\circ\text{C}$ .

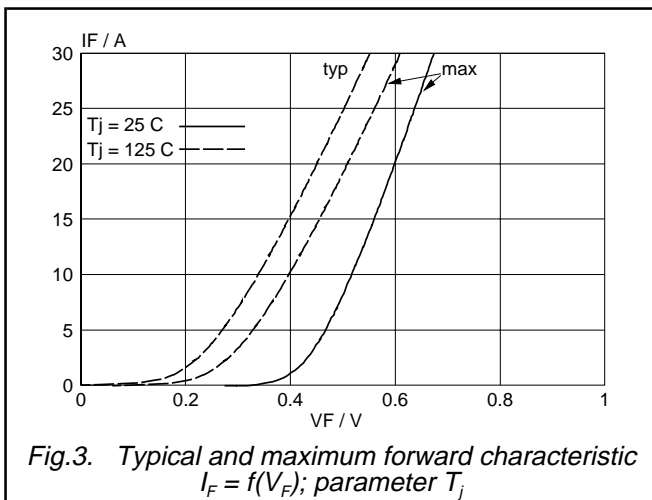


Fig.3. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_j$

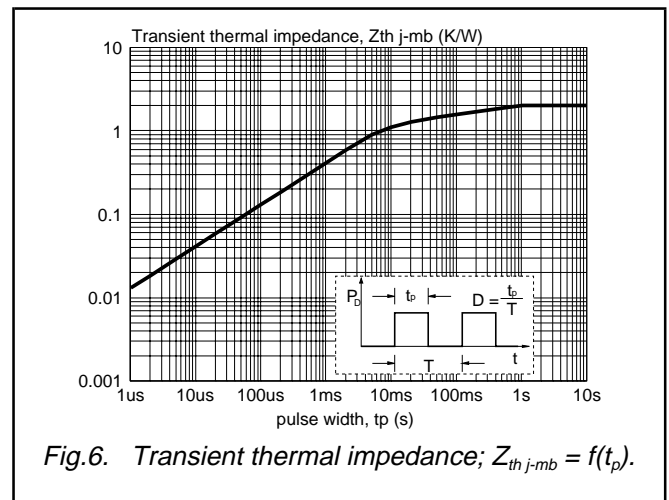
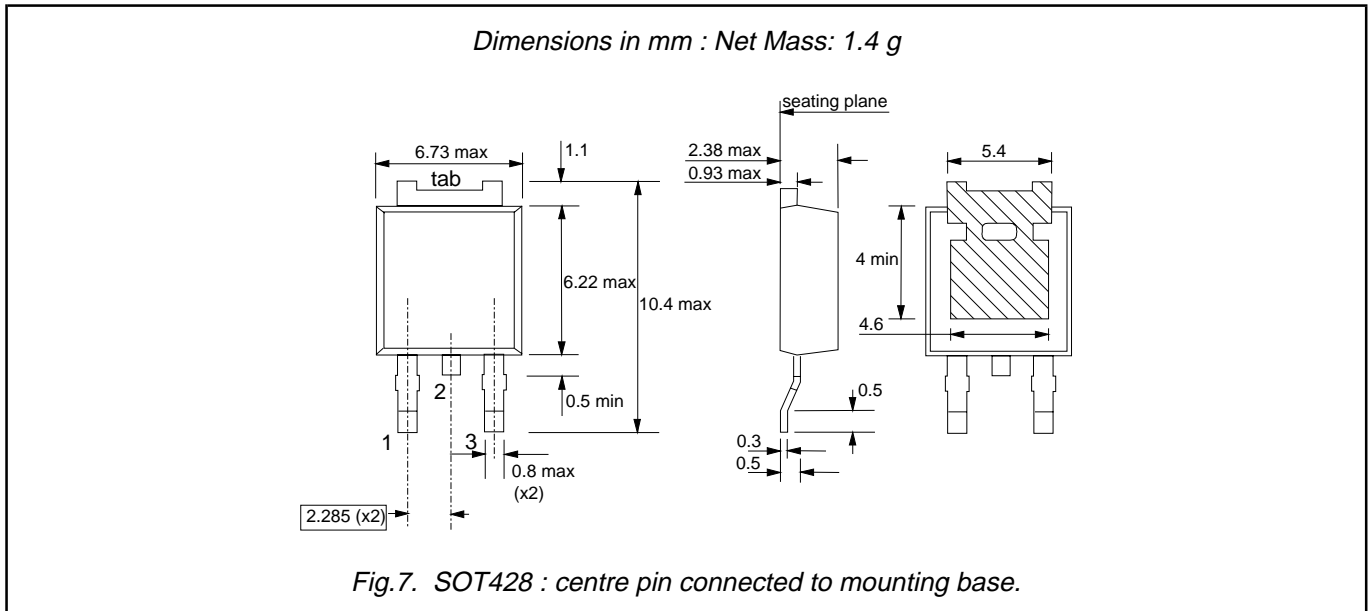


Fig.6. Transient thermal impedance;  $Z_{th\ j-mb} = f(t_p)$ .

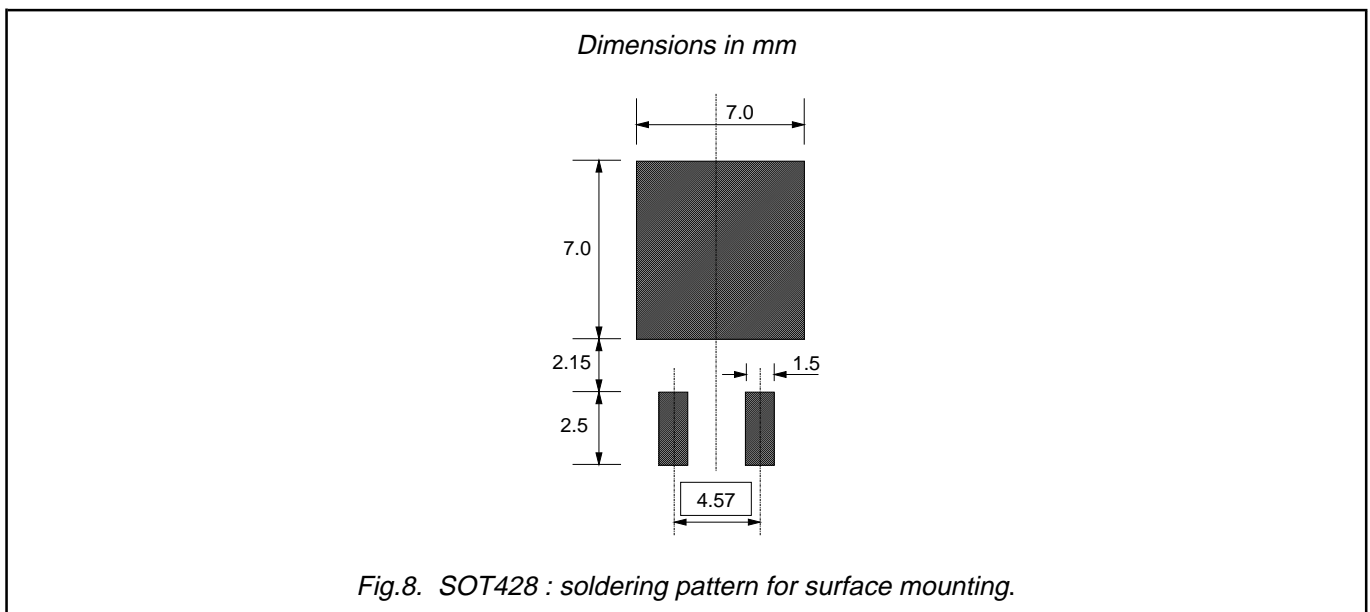
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**MECHANICAL DATA**



**MOUNTING INSTRUCTIONS**



**Notes**

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Epoxy meets UL94 V0 at 1/8".

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## DEFINITIONS

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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## LIFE SUPPORT APPLICATIONS

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